Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- · Direct triggering from low power drivers and logic ICs
- · High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- · Sensitive gate for easy logic level triggering
- Triggering in all four quadrants

3. Applications

- · General purpose motor controls
- General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 110 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	-	4	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	-	35	А
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics		,			
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. } 7}$	-	-	25	mA

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		N
3	G	gate		T2 — T1
mb	T2	mounting base; main terminal 2		sym051
			1 2 3	

6. Ordering information

Table 3. Ordering information

Type number	Package	ackage					
	Name	Description	Version				
BTA234-800E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; T _{mb} ≤ 110 °C; Fig. 1; Fig. 2; Fig. 3	-	4	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig 4; Fig 5	-	35	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	38.5	А
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	6.1	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 20 mA; T2+ G+	-	50	A/µs
		I _G = 20 mA; T2+ G-	-	50	A/µs
		I _G = 20 mA; T2- G-	-	50	A/µs
		I _G = 50 mA; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	Α
P_GM	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

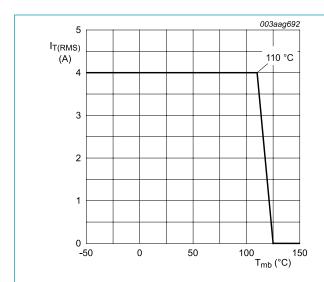
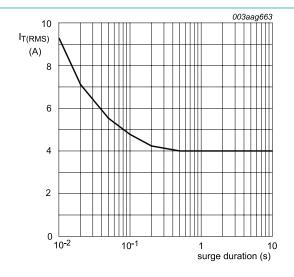


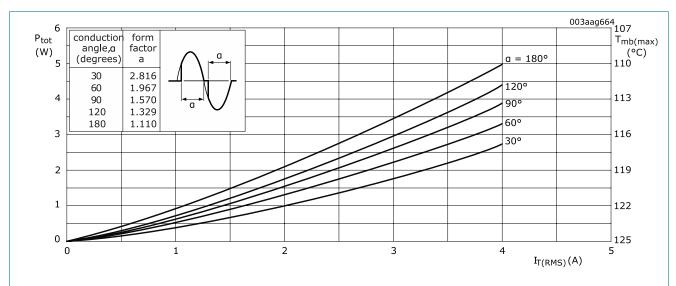
Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{mb} = 110 \text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

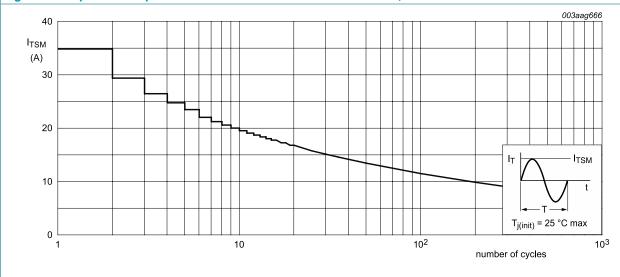
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 α = conduction angle

 $a = form factor = I_{T(RMS)} / I_{T(AV)}$

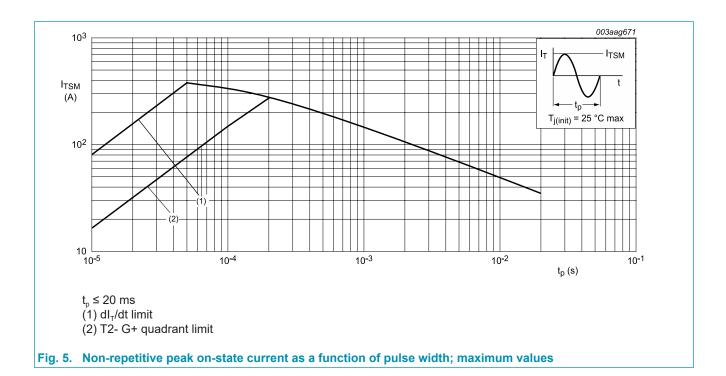
Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance	full cycle; Fig. 6	-	-	3.7	K/W
	from junction to mounting base	half cycle; <u>Fig. 6</u>	-	-	3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

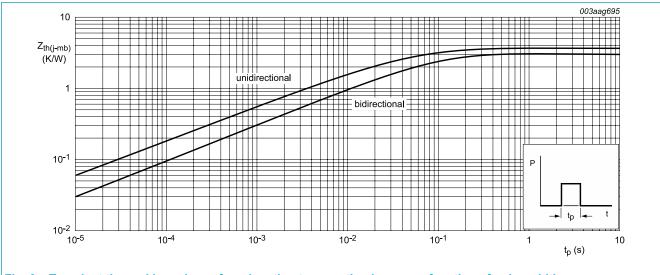


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

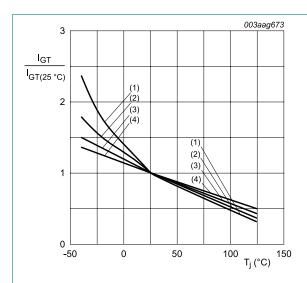
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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
l _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	-	25	mA
l _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \text{ Fig. 8}$	-	-	15	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V _T	on-state voltage	I _T = 6 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$	-	0.7	1	V
		V _D = 400V; I _T = 0.1 A;T _j = 25 °C; <u>Fig. 11</u>	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	80	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_D = 400 V; T_j = 125 °C; $dI_{com}/$ dt = 1.8 A/ms; I_T = 4 A; gate open circuit	15	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	V_D = 400 V; Tj = 125 C; $I_{T(RMS)}$ = 4 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	15	-	-	A/ms
t _{gt}	gate-controlled turn-on time	$I_{TM} = 6 \text{ A}; V_D = 800 \text{ V}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

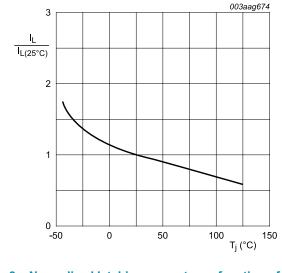


Fig. 8. Normalized latching current as a function of junction temperature

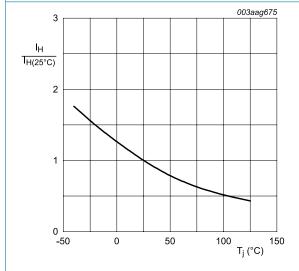
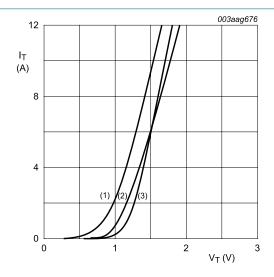


Fig. 9. Normalized holding current as a function of junction temperature



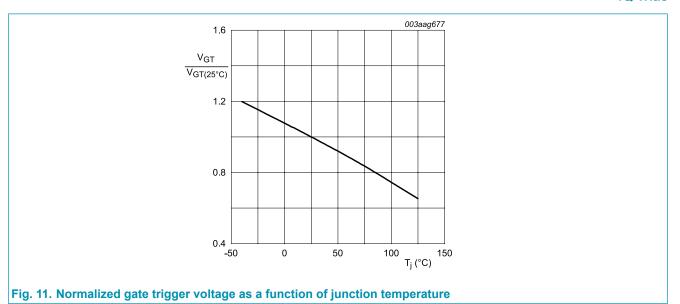
 V_o = 1.035 V; R_s = 0.078 Ω

(1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

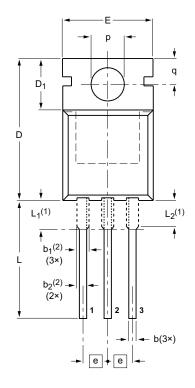
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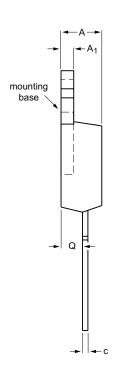


10. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78





0 5 10 mm

DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13	

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11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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For more information, please visit: http://www.ween-semi.com
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